

# 2SK2795

Silicon N-Channel MOS FET  
UHF Power Amplifier

# HITACHI

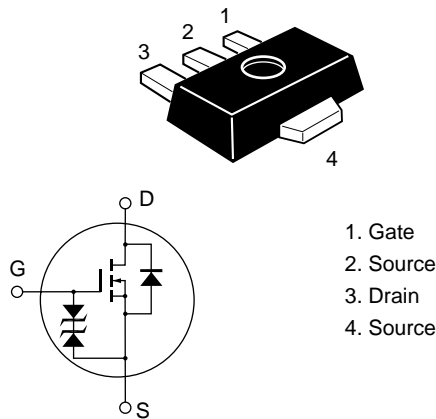
ADE-208-466A (Z)  
2nd. Edition  
Nov. 1996

## Features

- High power output, High gain, High efficiency  
PG = 11dB, Pout = 24dBm,  $\eta_D = 40\%$  min. (f = 836.5MHz)
- Compact package capable of surface mounting

## Outline

UPAK



This Device is sensitive to Electro Static Discharge.  
An Adequate handling procedure is requested.

**Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	10	V
Gate to source voltage	V <sub>GSS</sub>	±6	V
Drain current	I <sub>D</sub>	0.17	A
Drain peak current	I <sub>D(pulse)</sub> *1	0.3	A
Channel dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-45 to +150	°C

Notes: 1. PW ≤ 10ms, duty cycle ≤ 50 %

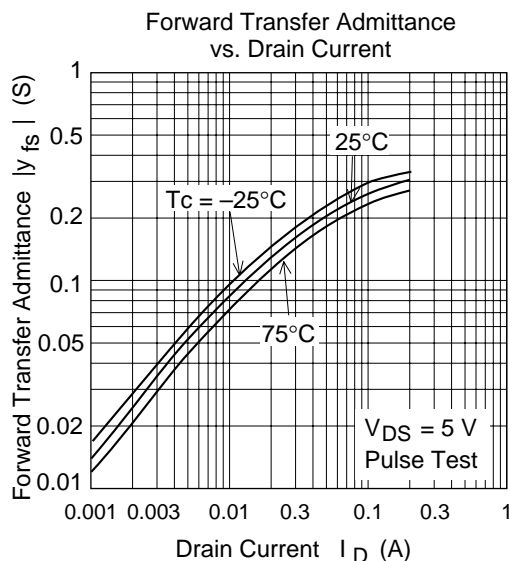
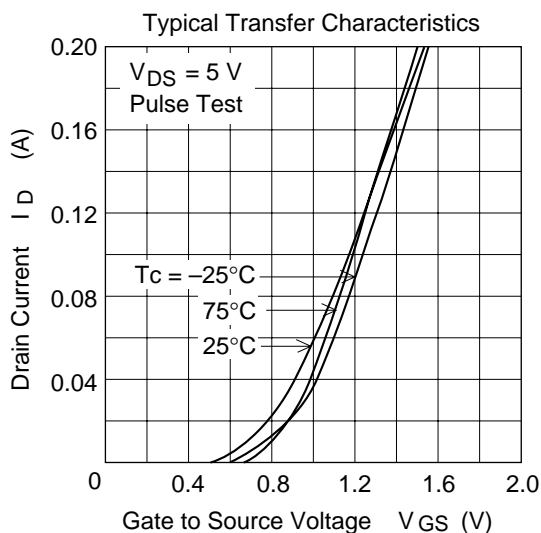
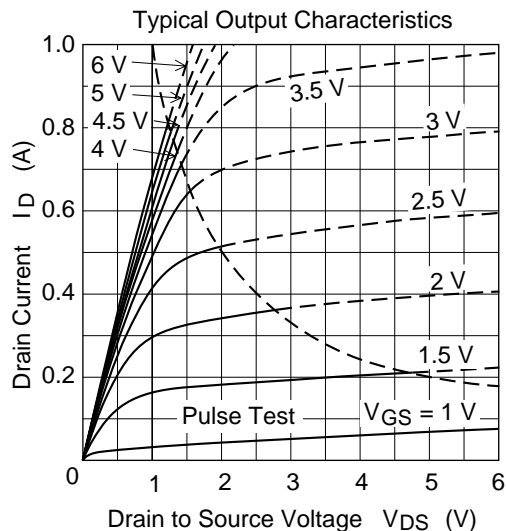
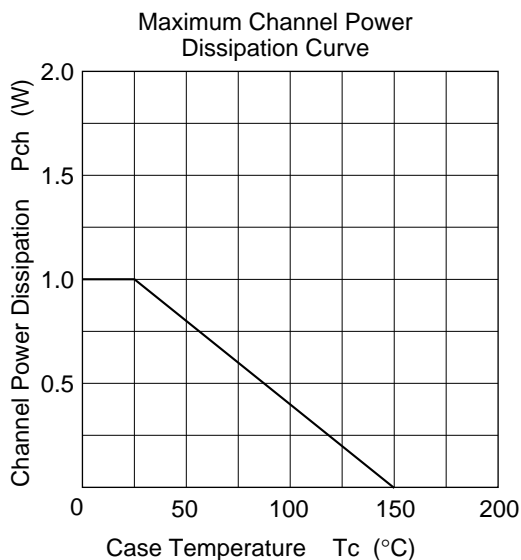
2. Value at Tc = 25°C

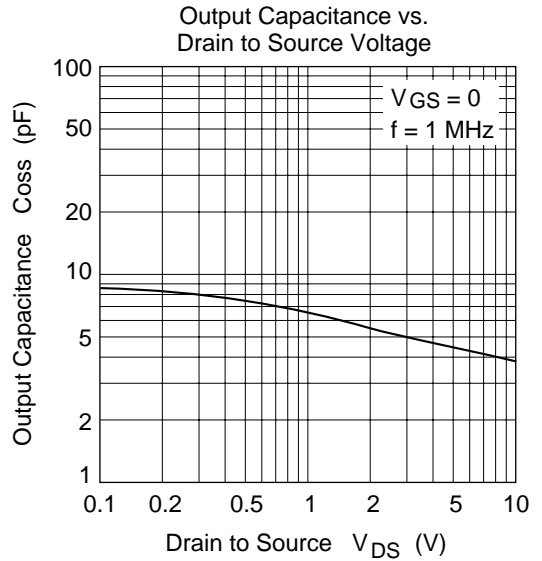
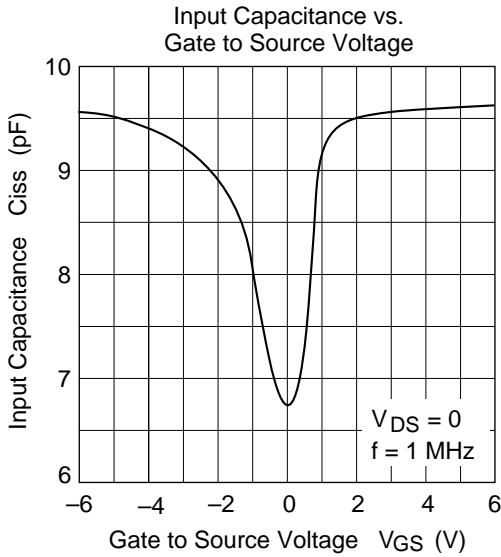
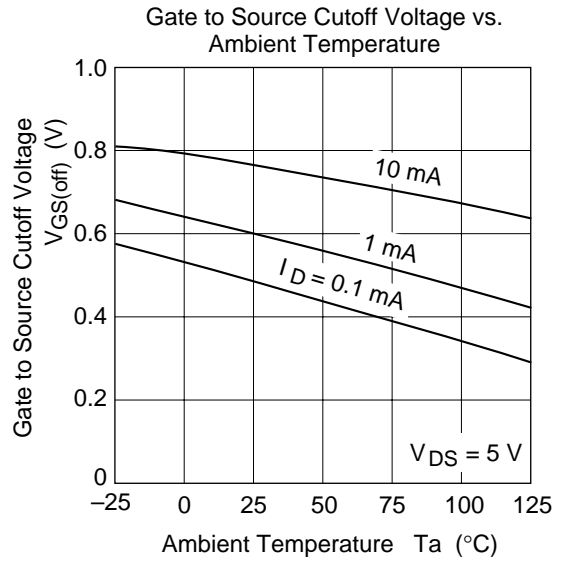
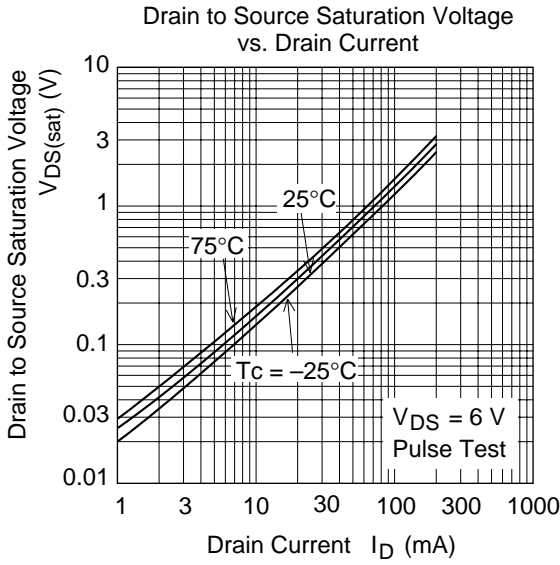
**Electrical Characteristics** (Ta = 25°C)

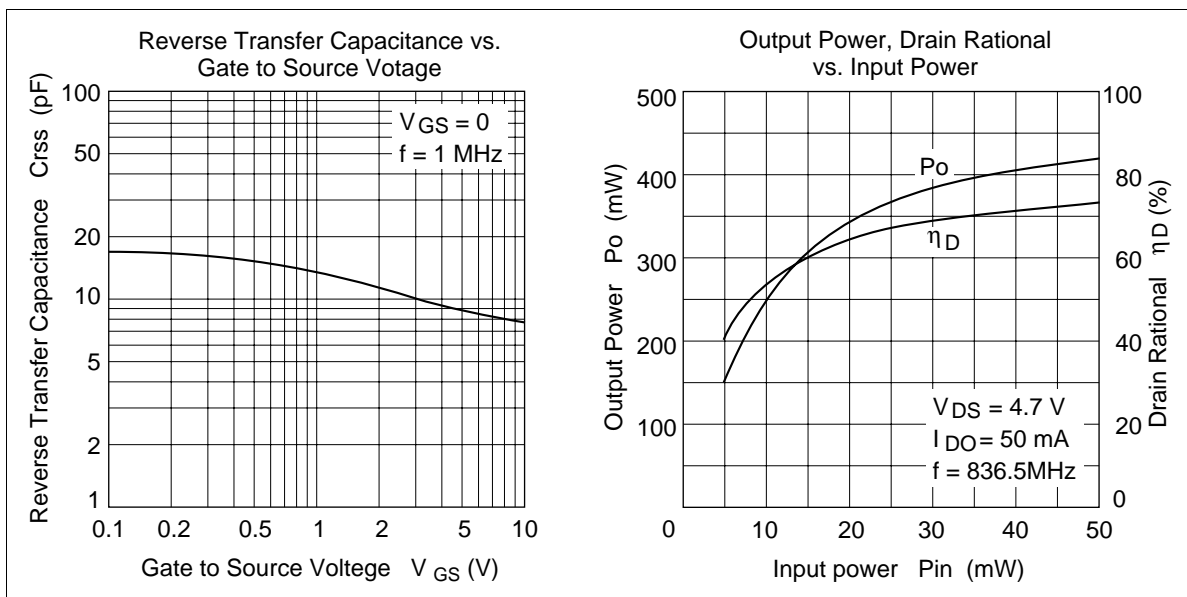
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	10	μA	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±5.0	μA	V <sub>GS</sub> = ±6V, V <sub>DS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	0.3	—	1.0	V	I <sub>D</sub> = 1mA, V <sub>DS</sub> = 5V
Input capacitance	Ciss	—	9.5	—	pF	V <sub>GS</sub> = 2V, V <sub>DS</sub> = 0 f = 1MHz
Output capacitance	Coss	—	4.5	—	pF	V <sub>DS</sub> = 5, V <sub>GS</sub> = 0 f = 1MHz
Output Power	Pout	24	—	—	dBm	V <sub>DS</sub> = 4.7V f = 836.5MHz Pin = 13dBm
Drain Rational	ηD	40	—	—	%	V <sub>DS</sub> = 4.7V f = 836.5MHz Pin = 13dBm

Note: 1. Marking is "DX".

## Main Characteristics

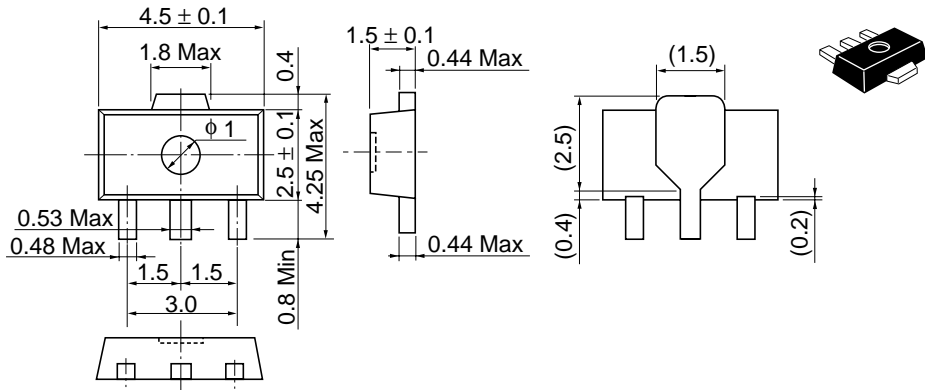






**Package Dimensions**

As of January, 2001  
Unit: mm



Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.050 g

## Cautions

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